Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	100	(buffer adj layer) near5 between near5 gate near5 (insulating or insulation or dielectric)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:27
L3	21	((buffer adj layer) near5 between near5 gate near5 (insulating or insulation or dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:27
L4	12	((buffer adj layer) near5 between near5 gate near5 (gate adj (insulating or insulation or dielectric))).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:28
L5	0	10/711473	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:30
L6	84851	(tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:30
L7	494	(tft or (thin adj film adj transistor)) and (buffer adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:30
L8	284	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:30
L9	163	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer).clm. and (gate adj (dielectric or insulating or insulation or isolation)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:30
L10	30	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer).clm. near10 (gate adj (dielectric or insulating or insulation or isolation)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:32

L11	9	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer).clm. near10 (gate adj (dielectric or insulating or insulation or isolation) near10 electrode).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:34
L12	9	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer).clm. near10 (gate adj (dielectric or insulating or insulation or isolation) near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:34
L13	114	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer) near10 (gate adj (dielectric or insulating or insulation or isolation) near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:35
L14	74	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer) near10 (dispose or disposing or disposed or form or forming or formed or formation) near5 (gate adj (dielectric or insulating or insulation or isolation) near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:35
L15	66	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 (gate adj (dielectric or insulating or insulation or isolation) near10 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:35
L16	48	(tft or (thin adj film adj transistor)).clm. and (buffer adj layer) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 (gate adj (dielectric or insulating or insulation or isolation) near5 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:35
L17	68	(tft or (thin adj film adj transistor)) and (buffer adj layer) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 (gate adj (dielectric or insulating or insulation or isolation) near5 electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:36

L18	63	(tft or (thin adj film adj transistor)) and (buffer adj layer) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 (gate adj (dielectric or insulating or insulation or isolation) near5 (gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:36
L19	0	(tft or (thin adj film adj transistor)) and (buffer adj layer) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near5 (gate adj (dielectric or insulating or insulation or isolation) near5 (gate adj electrode))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:36
L20	0	(tft or (thin adj film adj transistor)) and ((buffer adj layer) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near5 (gate adj (dielectric or insulating or insulation or isolation) near5 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:36
L21	3	(tft or (thin adj film adj transistor)) and ((buffer adj layer) near10 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near5 (gate adj (dielectric or insulating or insulation or isolation) near5 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:37
L22	3	(tft or (thin adj film adj transistor)) and ((buffer adj layer) near10 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near5 (gate adj (dielectric or insulating or insulation or isolation) near10 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:37
L23	5	(tft or (thin adj film adj transistor)) and ((buffer adj layer) near10 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near10 (gate adj (dielectric or insulating or insulation or isolation) near10 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:38

L24	26	((buffer adj layer) near10 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near10 (gate adj (dielectric or insulating or insulation or isolation) near10 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:38
L25	28	((buffer adj (film or layer)) near10 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near10 (gate adj (dielectric or insulating or insulation or isolation) near10 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:38
L26	13	((buffer adj (film or layer)) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near10 (gate adj (dielectric or insulating or insulation or isolation) near10 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:38
L27	8	((buffer adj (film or layer)) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near5 (gate adj (dielectric or insulating or insulation or isolation) near10 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:38
L28	5	((buffer adj (film or layer)) near5 (dispose or disposing or disposed or form or forming or formed or formation) near5 between near5 (gate adj (dielectric or insulating or insulation or isolation) near5 (gate adj electrode)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:39
L29	724	(between near2 (gate adj electrode) near2 (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:40
L30	542	(between near (gate adj electrode) near2 (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:40
L31	180	(between near (gate adj electrode) near (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:40

L32	0	buffer near5 (between near (gate adj electrode) near (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:40
L33	0	buffer near10 (between near (gate adj electrode) near (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:40
L34	27	buffer near10 ((gate adj electrode) near (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:41
L35	13	buffer near5 ((gate adj electrode) near (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:41
L36	4	buffer near2 ((gate adj electrode) near (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:41
L37	15	buffer near2 ((gate adj electrode) near2 (gate adj (dielectric or insulating or insulation or isolaion)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:46
L38	15	buffer near2 ((gate adj electrode) near2 (gate adj (dielectric or insulating or insulation or isolation)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:46
L39	41	buffer near5 ((gate adj electrode) near2 (gate adj (dielectric or insulating or insulation or isolation)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:46
L40	107	buffer near5 ((gate adj electrode) near5 (gate adj (dielectric or insulating or insulation or isolation)))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:46
L41	57	buffer near5 ((gate adj electrode) near5 (gate adj (dielectric or insulating or insulation or isolation))) and (tft or (thin adj film adj transistor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/21 19:50

| L42 | 0 | buffer near5 ((gate adj electrode) near5 (gate adj (dielectric or insulating or insulation or isolation))) and (tft or (thin adj film adj transistor)) and (low near temperature near polysilicon) | US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB | OR | ON | 2006/01/21 19:50 |